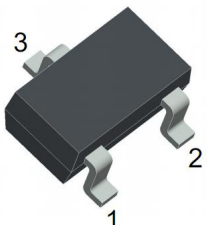

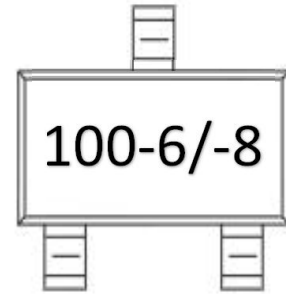
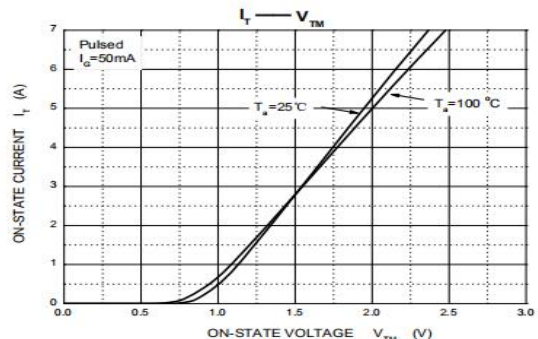
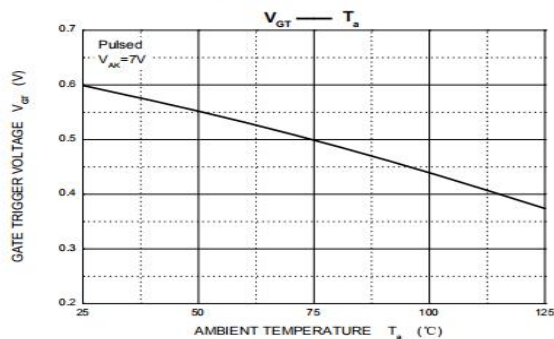
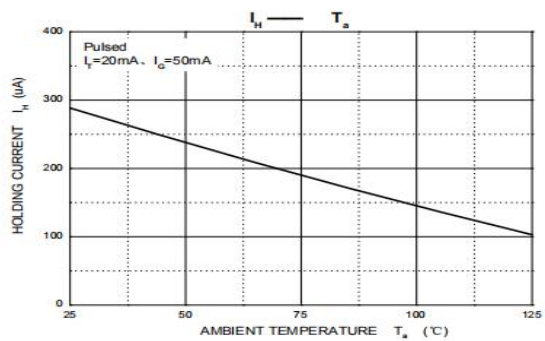
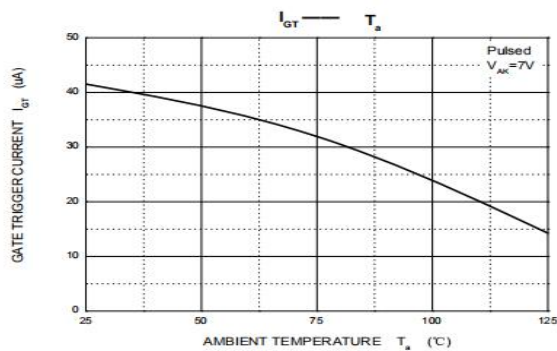


Silicon Controlled Rectifiers		SOT-23 Plastic-Encapsulate Transistors		
<p style="text-align: center;"><u>SOT-23</u></p>  <p>1.KATHODE 2.GATE 3.ANODE</p> <p>Equivalent Circuit:</p> 		<p>DESCRIPTION:</p> <p>These devices are intened to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits. Weight : 0.22 gram</p> <p>MARKING:</p> 		
MAXIMUM RATINGS (Ta=25°C unless otherwise noted)				
Rating	Symbol	MCR100-6	MCR100-8	Unit
Repetitive Peak Off-stage Voltage	VDRM	400	600	V
Collector-Base Voltage	ITRMS	0.8		A
Gate Trigger Current	IGT(Q1)	200		µA
Junction Temperature Range	TJ	+150		°C
Storage Temperature Range	TStg	-55 to +150		°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)						
Parameter	Symbol	Test Condition	Min	Max	Uni	
On state voltage	V _{TM} *	ITM=1A			V	
Gate trigger voltage	V _{GT}	V _{AK} =7V			V	
Peak Repetitive forward and reverse blocking voltage MCR100-6 MCR100-8	V _{DRM} AND V _{VRRM}	I _{DRM} =10μA	400 600		V	
Peak forward or reverse blocking Current	I _{DRM} I _{RRM}	V _{AK} =Rated V _{DRM} or V _{VRRM}		10	μA	
Holding current	I _H	I _{HL} =20mA V _{AK} =7V		5	mA	
Gate trigger current	I _{GT}	V _{AK} =7V	A2	5	15	μA
			A1	15	30	μA
			A	30	80	μA
			B	80	200	μA

* Forward current applied for 1 ms maximum duration, duty cycle ≤ 1%.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)